

YAMASAKI ET AL. - 10/673,648
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9. (Original) The method according to claim 8, wherein the inert gas comprises at least one Ar, He, Ne, Kr, Xe, and N₂.
10. (Original) The method according to claim 1, wherein the process gas includes the dilution gas comprising a reducing gas.
11. (Original) The method according to claim 10, wherein the reducing gas comprises H₂.
12. (Original) The method according to claim 1, wherein the metal-carbonyl gas flow rate is between about 0.1 sccm to about 200 sccm.
13. (Original) The method according to claim 4, wherein the carrier gas flow rate is less than about 1000 sccm.
14. (Original) The method according to claim 1, wherein the process gas includes the dilution gas having a flow rate less than about 2000 sccm.
15. (Original) The method according to claim 1, wherein the process gas flow rate is greater than about 400 sccm.
16. *de* (Original) The method according to claim 1, wherein the chamber pressure is less than about 200 mTorr.
17. (Original) The method according to claim 1, wherein the chamber pressure is less than about 100 mTorr.
18. (Original) The method according to claim 1, wherein the substrate temperature is less than about 500° C.
19. (Original) The method according to claim 1, wherein the substrate temperature is less than about 400° C.

9. The method according to claim 8, wherein the inert gas comprises at least one Ar, He, Ne, Kr, Xe, and N₂.

10. The method according to claim 1, wherein the process gas includes the dilution gas comprising a reducing gas.

11. The method according to claim 10, wherein the reducing gas comprises H₂.

12. The method according to claim 1, wherein the metal-carbonyl gas flow rate is between about 0.1 sccm to about 200 sccm.

13. The method according to claim 4, wherein the carrier gas flow rate is less than about 1000 sccm.

14. The method according to claim 1, wherein the process gas includes the dilution gas having a flow rate less than about 2000 sccm.

15. The method according to claim 1, wherein the process gas flow rate is greater than about 400 sccm.

16. The method according to claim 1, wherein the chamber pressure is less than about 200 mTorr.

17. The method according to claim 1, wherein the chamber pressure is less than about 100 mTorr.

18. The method according to claim 1, wherein the substrate temperature is less than about 500° C.

19. The method according to claim 1, wherein the substrate temperature is less than about 400° C.